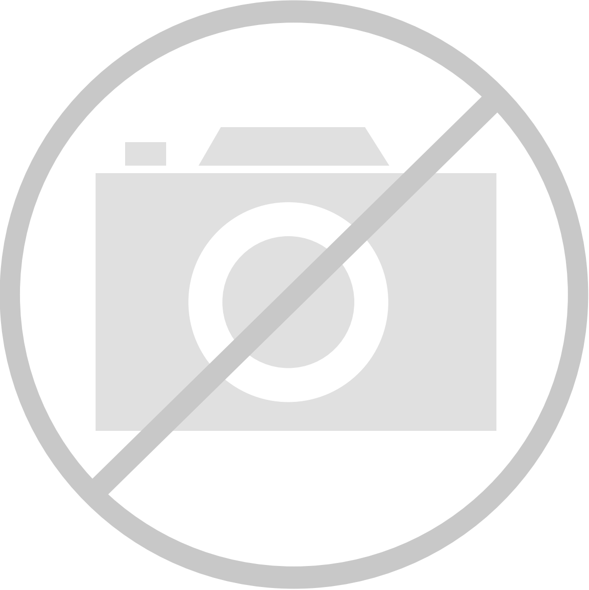
Microchip Technology - M1A3PE3000L-1FG896 Datasheet



Welcome to E-XFL.COM

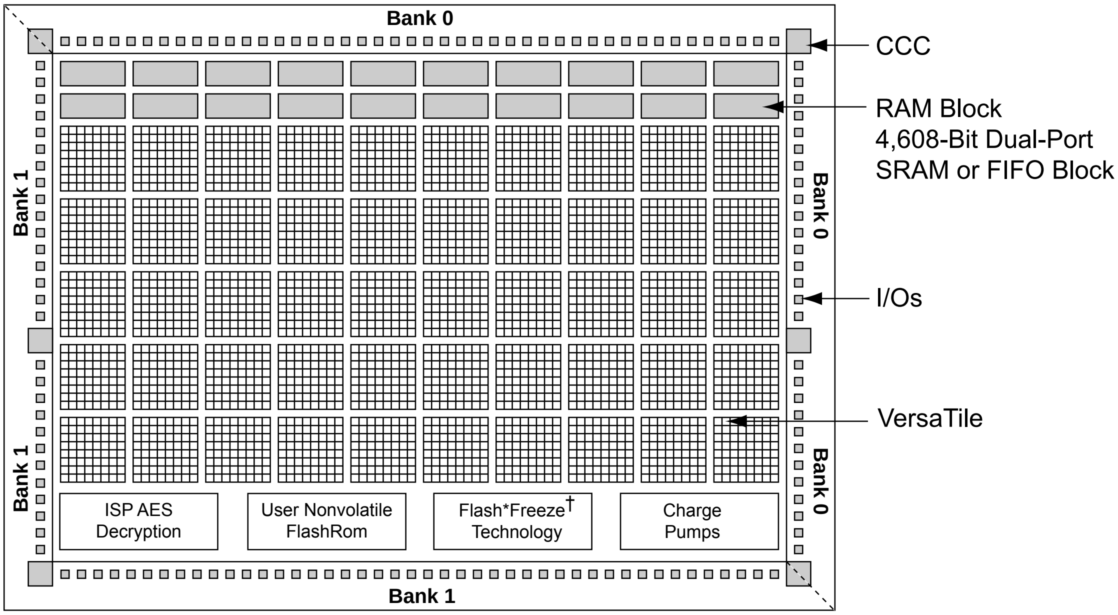
Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

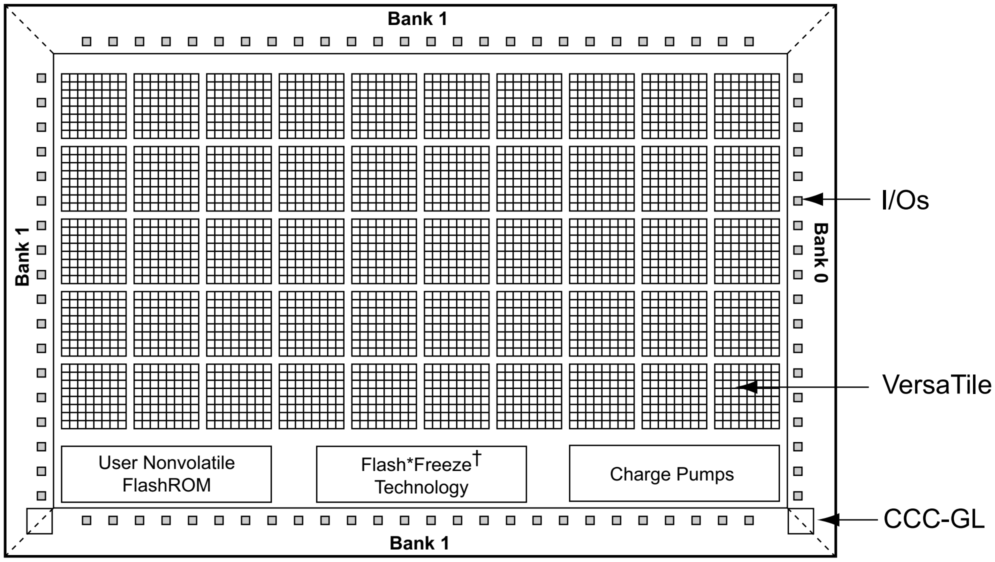
The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	516096
Number of I/O	620
Number of Gates	3000000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	896-BGA
Supplier Device Package	896-FBGA (31x31)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3pe3000l-1fg896



Note: † *Flash*Freeze mode is supported on IGLOO devices.*

***Figure 1-3* • IGLOO Device Architecture Overview with Two I/O Banks with RAM and PLL (60 k and 125 k gate densities)**



Note: † *Flash*Freeze mode is supported on IGLOO devices.*

***Figure 1-4* • IGLOO Device Architecture Overview with Three I/O Banks (AGLN015, AGLN020, A3PN015, and A3PN020)**

Global Resource Support in Flash-Based Devices

The flash FPGAs listed in Table 3-1 support the global resources and the functions described in this document.

***Table 3-1* • Flash-Based FPGAs**

Series	Family*	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
	IGLOO nano	The industry's lowest-power, smallest-size solution
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM® Cortex™-M1 soft processors, and flash memory into a monolithic device

Note: **The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.*

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO products as listed in Table 3-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 3-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

Design Recommendations

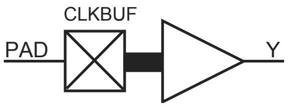
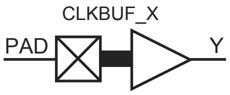
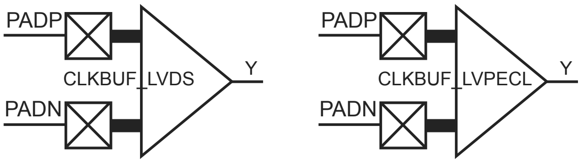
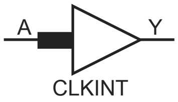
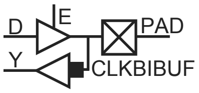
The following sections provide design flow recommendations for using a global network in a design.

- "Global Macros and I/O Standards"
- "Global Macro and Placement Selections" on page 64
- "Using Global Macros in Synplicity" on page 66
- "Global Promotion and Demotion Using PDC" on page 67
- "Spine Assignment" on page 68
- "Designer Flow for Global Assignment" on page 69
- "Simple Design Example" on page 71
- "Global Management in PLL Design" on page 73
- "Using Spines of Occupied Global Networks" on page 74

Global Macros and I/O Standards

The larger low power flash devices have six chip global networks and four quadrant global networks. However, the same clock macros are used for assigning signals to chip globals and quadrant globals. Depending on the clock macro placement or assignment in the Physical Design Constraint (PDC) file or MultiView Navigator (MVN), the signal will use the chip global network or quadrant network. Table 3-8 lists the clock macros available for low power flash devices. Refer to the *IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide* for details.

***Table 3-8* • Clock Macros**

Macro Name	Description	Symbol
CLKBUF	Input macro for Clock Network	
CLKBUF_x	Input macro for Clock Network with specific I/O standard	
CLKBUF_LVDS/LVPECL	LVDS or LVPECL input macro for Clock Network (not supported for IGLOO nano or ProASIC3 nano devices)	 PADP CLKBUF_LVDS Y PADN PADP CLKBUF_LVPECL Y PADN
CLKINT	Macro for internal clock interface	
CLKBIBUF	Bidirectional macro with input dedicated to routed Clock Network	

Use these available macros to assign a signal to the global network. In addition to these global macros, PLL and CLKDLY macros can also drive the global networks. Use I/O–standard–specific clock macros (CLKBUF_x) to instantiate a specific I/O standard for the global signals. Table 3-9 on page 63 shows the list of these I/O–standard–specific macros. Note that if you use these I/O–standard–specific clock macros, you cannot change the I/O standard later in the design stage. If you use the regular CLKBUF macro, you can use MVN or the PDC file in Designer to change the I/O standard. The default I/O

During Layout, Designer will assign two of the signals to quadrant global locations.

Step 3 (optional)

You can also assign the QCLK1_c and QCLK2_c nets to quadrant regions using the following PDC commands:

```
assign_local_clock –net QCLK1_c  –type quadrant UL
assign_local_clock –net QCLK2_c  –type quadrant LL
```

Step 4

Import this PDC with the netlist and run Compile again. You will see the following in the Compile report:

```
The following nets have been assigned to a global resource:
Fanout  Type          Name
--------------------------
1536    INT_NET       Net   : EN_ALL_c
                      Driver: EN_ALL_pad_CLKINT
                      Source: AUTO PROMOTED
1536    SET/RESET_NET Net   : ACLR_c
                      Driver: ACLR_pad_CLKINT
                      Source: AUTO PROMOTED
256     CLK_NET       Net   : QCLK3_c
                      Driver: QCLK3_pad_CLKINT
                      Source: AUTO PROMOTED
256     CLK_NET       Net   : $1N14
                      Driver: $1I5/Core
                      Source: ESSENTIAL
256     CLK_NET       Net   : $1N12
                      Driver: $1I6/Core
                      Source: ESSENTIAL
256     CLK_NET       Net   : $1N10
                      Driver: $1I6/Core
                      Source: ESSENTIAL
The following nets have been assigned to a quadrant clock resource using PDC:
Fanout  Type          Name
--------------------------
256     CLK_NET       Net   : QCLK1_c
                      Driver: QCLK1_pad_CLKINT
                      Region: quadrant_UL
256     CLK_NET       Net   : QCLK2_c
                      Driver: QCLK2_pad_CLKINT
                      Region: quadrant_LL
```

Step 5

Run Layout.

Global Management in PLL Design

This section describes the legal global network connections to PLLs in the low power flash devices. For detailed information on using PLLs, refer to "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" section on page 77. Microsemi recommends that you use the dedicated global pins to directly drive the reference clock input of the associated PLL for reduced propagation delays and clock distortion. However, low power flash devices offer the flexibility to connect other signals to reference clock inputs. Each PLL is associated with three global networks (Figure 3-5 on page 52). There are some limitations, such as when trying to use the global and PLL at the same time:

- If you use a PLL with only primary output, you can still use the remaining two free global networks.
- If you use three globals associated with a PLL location, you cannot use the PLL on that location.
- If the YB or YC output is used standalone, it will occupy one global, even though this signal does not go to the global network.

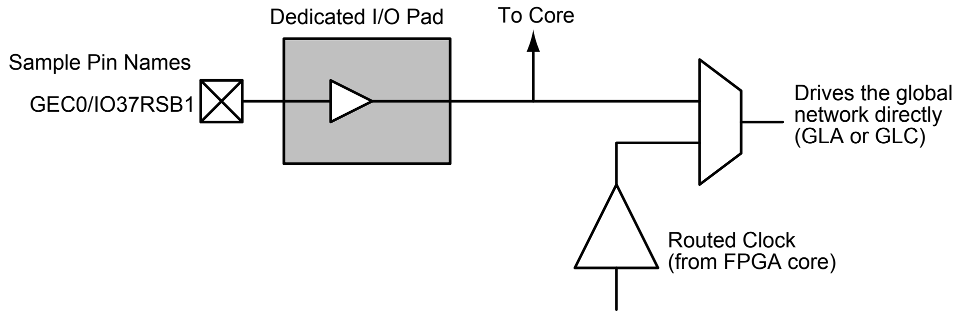
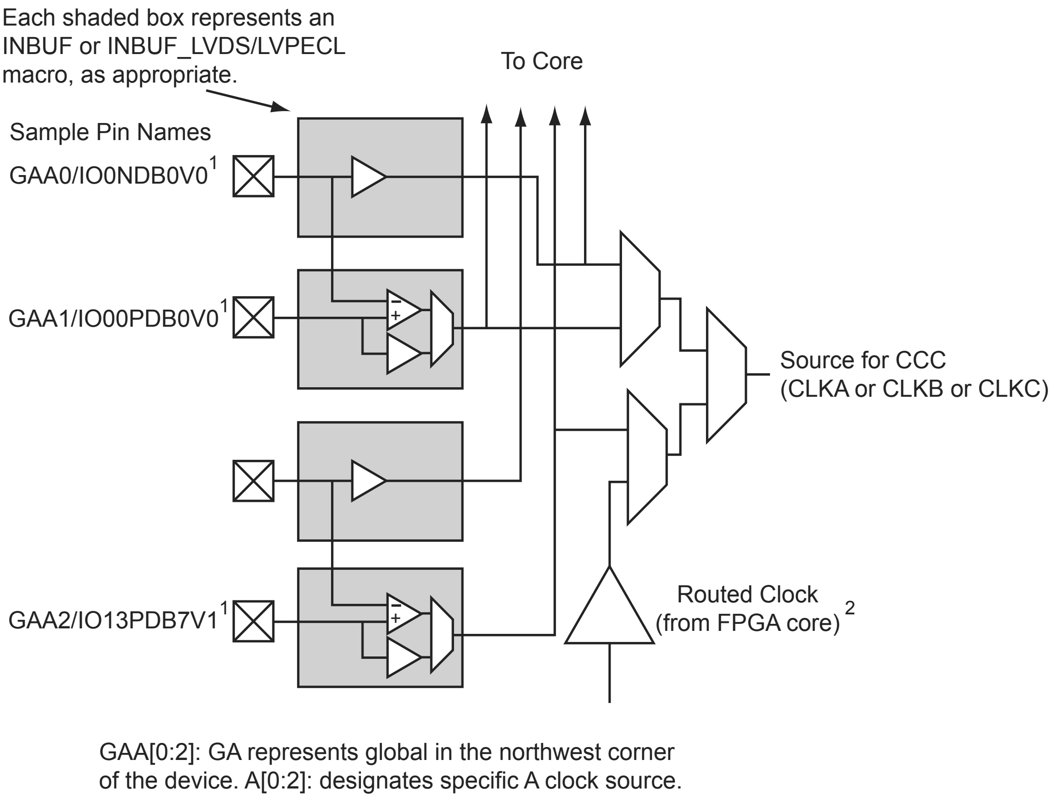


Figure 4-7 **• Clock Input Sources (30 k gates devices and below)**


Each shaded box represents an
INBUF or INBUF_LVDS/LVPECL
macro, as appropriate.
To Core
Sample Pin Names
GAA0/IO0NDB0V0 1
GAA1/IO00PDB0V0 1
GAA2/IO13PDB7V1 1
–
+
Source for CCC
(CLKA or CLKB or CLKC)
Routed Clock
(from FPGA core) 2
GAA[0:2]: GA represents global in the northwest corner
of the device. A[0:2]: designates specific A clock source.

Notes:

1. *Represents the global input pins. Globals have direct access to the clock conditioning block and are not routed via the FPGA fabric. Refer to the "User I/O Naming Conventions in I/O Structures" chapter of the appropriate device user's guide.*
2. *Instantiate the routed clock source input as follows:*
   a) *Connect the output of a logic element to the clock input of a PLL, CLKDLY, or CLKINT macro.*
   b) *Do not place a clock source I/O (INBUF or INBUF_LVPECL/LVDS/B-LVDS/M-LVDS/DDR) in a relevant global pin location.*
3. *IGLOO nano and ProASIC3 nano devices do not support differential inputs.*

Figure 4-8 **• Clock Input Sources Including CLKBUF, CLKBUF_LVDS/LVPECL, and CLKINT (60 k gates devices and above)**

Table 4-13 **• 2-Bit Feedback MUX**

FBSEL<1:0> State	MUX Input Selected
0	Ground. Used for power-down mode in power-down logic block.
1	PLL VCO 0° phase shift
2	PLL delayed VCO 0° phase shift
3	N/A

Table 4-14 **• Programmable Delay Selection for Feedback Delay and Secondary Core Output Delays**

FBDLY<4:0>; DLYYB<4:0>; DLYYC<4:0> State	Delay Value
0	Typical delay = 600 ps
1	Typical delay = 760 ps
2	Typical delay = 920 ps
⋮	⋮
31	Typical delay = 5.56 ns

Table 4-15 **• Programmable Delay Selection for Global Clock Output Delays**

DLYGLA<4:0>; DLYGLB<4:0>; DLYGLC<4:0> State	Delay Value
0	Typical delay = 225 ps
1	Typical delay = 760 ps
2	Typical delay = 920 ps
⋮	⋮
31	Typical delay = 5.56 ns

Table 4-16 **• Fusion Dynamic CCC Clock Source Selection**

RXASEL	DYNASEL	Source of CLKA
1	0	RC Oscillator
1	1	Crystal Oscillator
RXBSEL	**DYNBSEL**	**Source of CLKB**
1	0	RC Oscillator
1	1	Crystal Oscillator
RXBSEL	**DYNCSEL**	**Source of CLKC**
1	0	RC Oscillator
1	1	Crystal Oscillator

Table 4-17 **• Fusion Dynamic CCC NGMUX Configuration**

GLMUXCFG<1:0>	NGMUX Select Signal	Supported Input Clocks to NGMUX
00	0	GLA
	1	GLC
01	0	GLA
	1	GLINT
10	0	GLC
	1	GLINT

Features Supported on Every I/O

Table 7-5 lists all features supported by transmitter/receiver for single-ended and differential I/Os. Table 7-6 on page 180 lists the performance of each I/O technology.

***Table 7-5* • I/O Features**

Feature	Description
All I/O	• High performance (Table 7-6 on page 180) • Electrostatic discharge (ESD) protection • I/O register combining option
Single-Ended Transmitter Features	• Hot-swap: – 30K gate devices: hot-swap in every mode – All other IGLOO and ProASIC3 devices: no hot-swap • Output slew rate: 2 slew rates (except 30K gate devices) • Weak pull-up and pull-down resistors • Output drive: 3 drive strengths • Programmable output loading • Skew between output buffer enable/disable time: 2 ns delay on rising edge and 0 ns delay on falling edge (see the "Selectable Skew between Output Buffer Enable and Disable Times" section on page 199 for more information) • LVTTL/LVCMOS 3.3 V outputs compatible with 5 V TTL inputs
Single-Ended Receiver Features	• 5 V–input–tolerant receiver (Table 7-12 on page 193) • Separate ground plane for GNDQ pin and power plane for VMV pin are used for input buffer to reduce output-induced noise.
Differential Receiver Features—250K through 1M Gate Devices	• Separate ground plane for GNDQ pin and power plane for VMV pin are used for input buffer to reduce output-induced noise.
CMOS-Style LVDS, B-LVDS, M-LVDS, or LVPECL Transmitter	• Two I/Os and external resistors are used to provide a CMOS-style LVDS, DDR LVDS, B-LVDS, and M-LVDS/LVPECL transmitter solution. • High slew rate • Weak pull-up and pull-down resistors • Programmable output loading

B-LVDS/M-LVDS

Bus LVDS (B-LVDS) refers to bus interface circuits based on LVDS technology. Multipoint LVDS (M-LVDS) specifications extend the LVDS standard to high-performance multipoint bus applications. Multidrop and multipoint bus configurations may contain any combination of drivers, receivers, and transceivers. Microsemi LVDS drivers provide the higher drive current required by B-LVDS and M-LVDS to accommodate the loading. The driver requires series terminations for better signal quality and to control voltage swing. Termination is also required at both ends of the bus, since the driver can be located anywhere on the bus. These configurations can be implemented using TRIBUF_LVDS and BIBUF_LVDS macros along with appropriate terminations. Multipoint designs using Microsemi LVDS macros can achieve up to 200 MHz with a maximum of 20 loads. A sample application is given in Figure 8-9. The input and output buffer delays are available in the LVDS sections in the datasheet.

Example: For a bus consisting of 20 equidistant loads, the terminations given in EQ 8-1 provide the required differential voltage, in worst case industrial operating conditions, at the farthest receiver:

$$R_S = 60\ \Omega,\ R_T = 70\ \Omega,\ \text{given } Z_O = 50\ \Omega\ (2'')\ \text{and } Z_{stub} = 50\ \Omega\ (\sim 1.5'').$$

EQ 8-1

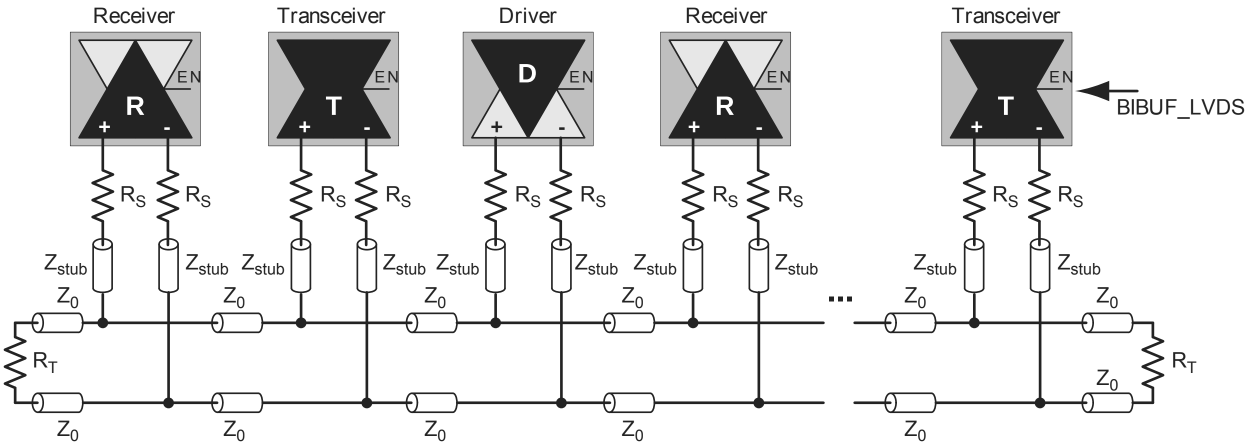


Figure 8-9 • **A B-LVDS/M-LVDS Multipoint Application Using LVDS I/O Buffers**

Date	Changes	Page
v1.3 (October 2008)	The "Low Power Flash Device I/O Support" section was revised to include new families and make the information more concise.	214
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 8-1 · Flash-Based FPGAs: • ProASIC3L was updated to include 1.5 V. • The number of PLLs for ProASIC3E was changed from five to six.	214
v1.1 (March 2008)	This document was previously part of *I/O Structures in IGLOO and ProASIC3 Devices*. To provide information specific to IGLOOe, ProASIC3E, and ProASIC3EL, the content was separated and made into a new document. For information on other low power flash family I/O structures, refer to the following documents: *I/O Structures in IGLOO and ProASIC3 Devices* contains information specific to IGLOO, ProASIC3, and ProASIC3L I/O features. *I/O Structures in IGLOO PLUS Devices* contains information specific to IGLOO PLUS I/O features.	N/A

Software-Controlled I/O Attributes

Users may modify these programmable I/O attributes using the I/O Attribute Editor. Modifying an I/O attribute may result in a change of state in Designer. Table 9-2 details which steps have to be re-run as a function of modified I/O attribute.

Table 9-2 **• Designer State (resulting from I/O attribute modification)**

I/O Attribute	**Designer States[1]**				
	Compile	**Layout**	**Fuse**	**Timing**	**Power**
Slew Control[2]	No	No	Yes	Yes	Yes
Output Drive (mA)	No	No	Yes	Yes	Yes
Skew Control	No	No	Yes	Yes	Yes
Resistor Pull	No	No	Yes	Yes	Yes
Input Delay	No	No	Yes	Yes	Yes
Schmitt Trigger	No	No	Yes	Yes	Yes
OUT_LOAD	No	No	No	Yes	Yes
COMBINE_REGISTER	Yes	Yes	N/A	N/A	N/A

Notes:

1. *No = Remains the same, Yes = Re-run the step, N/A = Not applicable*
2. *Skew control does not apply to IGLOO nano, IGLOO PLUS, and ProASIC3 nano devices.*
3. *Programmable input delay is applicable only for ProASIC3E, ProASIC3EL, RT ProASIC3, and IGLOOe devices.*

Implementing I/Os in Microsemi Software

Microsemi Libero SoC software is integrated with design entry tools such as the SmartGen macro builder, the ViewDraw schematic entry tool, and an HDL editor. It is also integrated with the synthesis and Designer tools. In this section, all necessary steps to implement the I/Os are discussed.

Design Entry

There are three ways to implement I/Os in a design:

1. Use the SmartGen macro builder to configure I/Os by generating specific I/O library macros and then instantiating them in top-level code. This is especially useful when creating I/O bus structures.
2. Use an I/O buffer cell in a schematic design.
3. Manually instantiate specific I/O macros in the top-level code.

If technology-specific macros, such as INBUF_LVCMOS33 and OUTBUF_PCI, are used in the HDL code or schematic, the user will not be able to change the I/O standard later on in Designer. If generic I/O macros are used, such as INBUF, OUTBUF, TRIBUF, CLKBUF, and BIBUF, the user can change the I/O standard using the Designer I/O Attribute Editor tool.

Using SmartGen for I/O Configuration

The SmartGen tool in Libero SoC provides a GUI-based method of configuring the I/O attributes. The user can select certain I/O attributes while configuring the I/O macro in SmartGen. The steps to configure an I/O macro with specific I/O attributes are as follows:

1. Open Libero SoC.
2. On the left-hand side of the Catalog View, select **I/O**, as shown in Figure 9-2.

Figure 9-2 **• SmartGen Catalog**

those banks, the user does not need to assign the same VCCI voltage to another bank. The user needs to assign the other three VCCI voltages to three more banks.

Assigning Technologies and VREF to I/O Banks

Low power flash devices offer a wide variety of I/O standards, including voltage-referenced standards. Before proceeding to Layout, each bank must have the required VCCI voltage assigned for the corresponding I/O technologies used for that bank. The voltage-referenced standards require the use of a reference voltage (VREF). This assignment can be done manually or automatically. The following sections describe this in detail.

Manually Assigning Technologies to I/O Banks

The user can import the PDC at this point and resolve this requirement. The PDC command is

```
set_iobank [bank name] –vcci [vcci value]
```

Another method is to use the I/O Bank Settings dialog box (**MVN** > **Edit** > **I/O Bank Settings**) to set up the V_{CCI} voltage for the bank (Figure 9-12).

Figure 9-12 **• Setting VCCI for a Bank**

10 – DDR for Microsemi's Low Power Flash Devices

Introduction

The I/Os in Fusion, IGLOO, and ProASIC3 devices support Double Data Rate (DDR) mode. In this mode, new data is present on every transition (or clock edge) of the clock signal. This mode doubles the data transfer rate compared with Single Data Rate (SDR) mode, where new data is present on one transition (or clock edge) of the clock signal. Low power flash devices have DDR circuitry built into the I/O tiles. I/Os are configured to be DDR receivers or transmitters by instantiating the appropriate special macros (examples shown in Figure 10-4 on page 276 and Figure 10-5 on page 277) and buffers (DDR_OUT or DDR_REG) in the RTL design. This document discusses the options the user can choose to configure the I/Os in this mode and how to instantiate them in the design.

Double Data Rate (DDR) Architecture

Low power flash devices support 350 MHz DDR inputs and outputs. In DDR mode, new data is present on every transition of the clock signal. Clock and data lines have identical bandwidths and signal integrity requirements, making them very efficient for implementing very high-speed systems. High-speed DDR interfaces can be implemented using LVDS (not applicable for IGLOO nano and ProASIC3 nano devices). In IGLOOe, ProASIC3E, AFS600, and AFS1500 devices, DDR interfaces can also be implemented using the HSTL, SSTL, and LVPECL I/O standards. The DDR feature is primarily implemented in the FPGA core periphery and is not tied to a specific I/O technology or limited to any I/O standard.

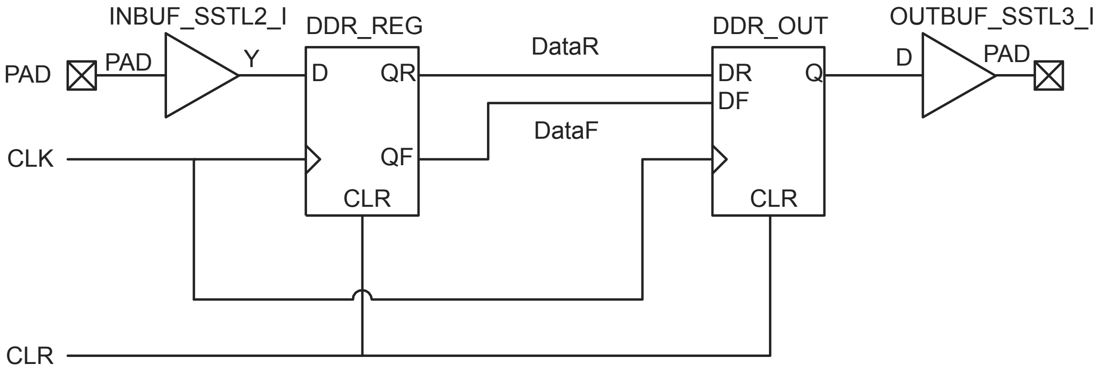


Figure 10-1 • **DDR Support in Low Power Flash Devices**

Figure 10-11 • **DDR Input/Output Cells as Seen by ChipPlanner for IGLOO/e Devices**

Verilog

```
module Inbuf_ddr(PAD,CLR,CLK,QR,QF);

input PAD, CLR, CLK;
output  QR, QF;

wire Y;

  DDR_REG DDR_REG_0_inst(.D(Y), .CLK(CLK), .CLR(CLR), .QR(QR), .QF(QF));
  INBUF INBUF_0_inst(.PAD(PAD), .Y(Y));

endmodule

module Outbuf_ddr(DataR,DataF,CLR,CLK,PAD);

input DataR, DataF, CLR, CLK;
output  PAD;

wire Q, VCC;

  VCC VCC_1_net(.Y(VCC));
  DDR_OUT DDR_OUT_0_inst(.DR(DataR), .DF(DataF), .CLK(CLK), .CLR(CLR), .Q(Q));
  OUTBUF OUTBUF_0_inst(.D(Q), .PAD(PAD));

endmodule
```

Related Documents

Below is a list of related documents, their location on the Microsemi SoC Products Group website, and a brief summary of each document.

Application Notes

Programming Antifuse Devices

http://www.microsemi.com/soc/documents/AntifuseProgram_AN.pdf

Implementation of Security in Actel's ProASIC and ProASIC^{PLUS} Flash-Based FPGAs

http://www.microsemi.com/soc/documents/Flash_Security_AN.pdf

User's Guides

FlashPro Programmers

FlashPro4,[1] FlashPro3, FlashPro Lite, and FlashPro[2]

http://www.microsemi.com/soc/products/hardware/program_debug/flashpro/default.aspx

FlashPro User's Guide

http://www.microsemi.com/soc/documents/FlashPro_UG.pdf

The FlashPro User's Guide includes hardware and software setup, self-test instructions, use instructions, and a troubleshooting / error message guide.

Silicon Sculptor 3 and Silicon Sculptor II

http://www.microsemi.com/soc/products/hardware/program_debug/ss/default.aspx

Other Documents

http://www.microsemi.com/soc/products/solutions/security/default.aspx#flashlock

The security resource center describes security in Microsemi Flash FPGAs.

Quality and Reliability Guide

http://www.microsemi.com/soc/documents/RelGuide.pdf

Programming and Functional Failure Guidelines

http://www.microsemi.com/soc/documents/FA_Policies_Guidelines_5-06-00002.pdf

[1] *FlashPro4 replaced FlashPro3 in Q1 2010.*
[2] *FlashPro is no longer available.*

List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
July 2010	FlashPro4 is a replacement for FlashPro3 and has been added to this chapter. FlashPro is no longer available.	N/A
	The chapter was updated to include SmartFusion devices.	N/A
	The following were deleted: "Live at Power-Up (LAPU) or Boot PROM" section "Design Security" section Table 14-2 • Programming Features for Actel Devices and much of the text in the "Programming Features for Microsemi Devices" section "Programming Flash FPGAs" section "Return Material Authorization (RMA) Policies" section	N/A
	The "Device Programmers" section was revised.	291
	The Independent Programming Centers information was removed from the "Volume Programming Services" section.	292
	Table 11-3 • Programming Solutions was revised to add FlashPro4 and note that FlashPro is discontinued. A note was added for FlashPro Lite regarding power supply requirements.	293
	Most items were removed from Table 11-4 • Programming Ordering Codes, including FlashPro3 and FlashPro.	294
	The "Programmer Device Support" section was deleted and replaced with a reference to the Microsemi SoC Products Group website for the latest information.	294
	The "Certified Programming Solutions" section was revised to add FlashPro4 and remove Silicon Sculptor I and Silicon Sculptor 6X. Reference to *Programming and Functional Failure Guidelines* was added.	294
	The file type *.pdb was added to the "Use the Latest Version of the Designer Software to Generate Your Programming File (recommended)" section.	295
	Instructions on cleaning and careful insertion were added to the "Perform Routine Hardware Self-Diagnostic Test" section. Information was added regarding testing Silicon Sculptor programmers with an adapter module installed before every programming session verifying their calibration annually.	295
	The "Signal Integrity While Using ISP" section is new.	296
	The "Programming Failure Allowances" section was revised.	296

Cortex-M1 Device Security

Cortex-M1–enabled devices are shipped with the following security features:

- FPGA array enabled for AES-encrypted programming and verification
- FlashROM enabled for AES-encrypted Write and Verify
- Fusion Embedded Flash Memory enabled for AES-encrypted Write

AES Encryption of Programming Files

Low power flash devices employ AES as part of the security mechanism that prevents invasive and noninvasive attacks. The mechanism entails encrypting the programming file with AES encryption and then passing the programming file through the AES decryption core, which is embedded in the device. The file is decrypted there, and the device is successfully programmed. The AES master key is stored in on-chip nonvolatile memory (flash). The AES master key can be preloaded into parts in a secure programming environment (such as the Microsemi In-House Programming center), and then "blank" parts can be shipped to an untrusted programming or manufacturing center for final personalization with an AES-encrypted bitstream. Late-stage product changes or personalization can be implemented easily and securely by simply sending a STAPL file with AES-encrypted data. Secure remote field updates over public networks (such as the Internet) are possible by sending and programming a STAPL file with AES-encrypted data.

The AES key protects the programming data for file transfer into the device with 128-bit AES encryption. If AES encryption is used, the AES key is stored or preprogrammed into the device. To program, you must use an AES-encrypted file, and the encryption used on the file must match the encryption key already in the device.

The AES key is protected by a FlashLock security Pass Key that is also implemented in each device. The AES key is always protected by the FlashLock Key, and the AES-encrypted file does NOT contain the FlashLock Key. This FlashLock Pass Key technology is exclusive to the Microsemi flash-based device families. FlashLock Pass Key technology can also be implemented without the AES encryption option, providing a choice of different security levels.

In essence, security features can be categorized into the following three options:

- AES encryption with FlashLock Pass Key protection
- FlashLock protection only (no AES encryption)
- No protection

Each of the above options is explained in more detail in the following sections with application examples and software implementation options.

Advanced Encryption Standard

The 128-bit AES standard (FIPS-192) block cipher is the NIST (National Institute of Standards and Technology) replacement for DES (Data Encryption Standard FIPS46-2). AES has been designed to protect sensitive government information well into the 21st century. It replaces the aging DES, which NIST adopted in 1977 as a Federal Information Processing Standard used by federal agencies to protect sensitive, unclassified information. The 128-bit AES standard has 3.4×10^{38} possible 128-bit key variants, and it has been estimated that it would take 1,000 trillion years to crack 128-bit AES cipher text using exhaustive techniques. Keys are stored (securely) in low power flash devices in nonvolatile flash memory. All programming files sent to the device can be authenticated by the part prior to programming to ensure that bad programming data is not loaded into the part that may possibly damage it. All programming verification is performed on-chip, ensuring that the contents of low power flash devices remain secure.

Microsemi has implemented the 128-bit AES (Rijndael) algorithm in low power flash devices. With this key size, there are approximately 3.4×10^{38} possible 128-bit keys. DES has a 56-bit key size, which provides approximately 7.2×10^{16} possible keys. In their AES fact sheet, the National Institute of Standards and Technology uses the following hypothetical example to illustrate the theoretical security provided by AES. If one were to assume that a computing system existed that could recover a DES key in a second, it would take that same machine approximately 149 trillion years to crack a 128-bit AES key. NIST continues to make their point by stating the universe is believed to be less than 20 billion years old.[1]

Figure 12-10 **• All Silicon Features Selected for IGLOO and ProASIC3 Devices**

Figure 12-11 **• All Silicon Features Selected for Fusion**

18 – Power-Up/-Down Behavior of Low Power Flash Devices

Introduction

Microsemi's low power flash devices are flash-based FPGAs manufactured on a 0.13 µm process node. These devices offer a single-chip, reprogrammable solution and support Level 0 live at power-up (LAPU) due to their nonvolatile architecture.

Microsemi's low power flash FPGA families are optimized for logic area, I/O features, and performance. IGLOO® devices are optimized for power, making them the industry's lowest power programmable solution. IGLOO PLUS FPGAs offer enhanced I/O features beyond those of the IGLOO ultra-low power solution for I/O-intensive low power applications. IGLOO nano devices are the industry's lowest-power cost-effective solution. ProASIC3®L FPGAs balance low power with high performance. The ProASIC3 family is Microsemi's high-performance flash FPGA solution. ProASIC3 nano devices offer the lowest-cost solution with enhanced I/O capabilities.

Microsemi's low power flash devices exhibit very low transient current on each power supply during power-up. The peak value of the transient current depends on the device size, temperature, voltage levels, and power-up sequence.

The following devices can have inputs driven in while the device is not powered:

- IGLOO (AGL015 and AGL030)
- IGLOO nano (all devices)
- IGLOO PLUS (AGLP030, AGLP060, AGLP125)
- IGLOOe (AGLE600, AGLE3000)
- ProASIC3L (A3PE3000L)
- ProASIC3 (A3P015, A3P030)
- ProASIC3 nano (all devices)
- ProASIC3E (A3PE600, A3PE1500, A3PE3000)
- Military ProASIC3EL (A3PE600L, A3PE3000L, but not A3P1000)
- RT ProASIC3 (RT3PE600L, RT3PE3000L)

The driven I/Os do not pull up power planes, and the current draw is limited to very small leakage current, making them suitable for applications that require cold-sparing. These devices are hot-swappable, meaning they can be inserted in a live power system.[1]

[1] *For more details on the levels of hot-swap compatibility in Microsemi's low power flash devices, refer to the "Hot-Swap Support" section in the I/O Structures chapter of the FPGA fabric user's guide for the device you are using.*

Revision (month/year)	**Chapter Affected**	**List of Changes (page number)**
Revision 0 (continued)	"DDR for Microsemi’s Low Power Flash Devices" was revised.	285
	"Programming Flash Devices" was revised.	298
	"In-System Programming (ISP) of Microsemi’s Low Power Flash Devices Using FlashPro4/3/3X" was revised.	339
	"Core Voltage Switching Circuit for IGLOO and ProASIC3L In-System Programming" was revised.	347
	"Boundary Scan in Low Power Flash Devices" was revised.	362